

WET BENCH: OXIDE ETCH + HYDROPHILIC CLEAN (RCA CLEAN)

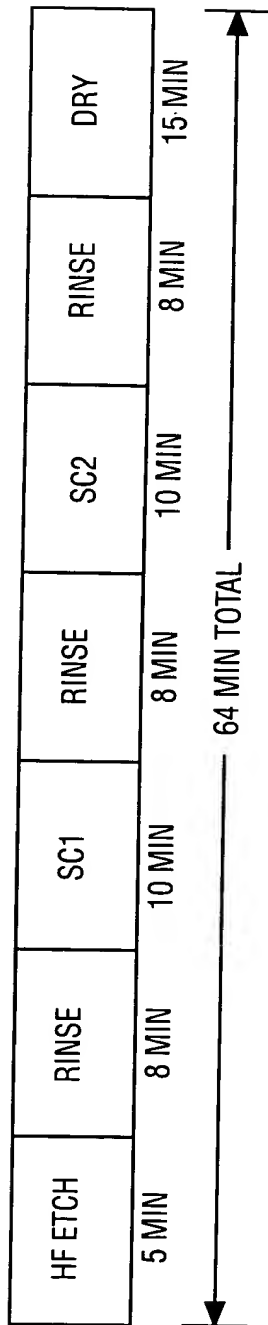


FIG. 1a

SINGLE WAFER CLEANING TOOL SINGLE STEP CLEAN
OXIDE ETCH + HYDROPHILIC CLEAN

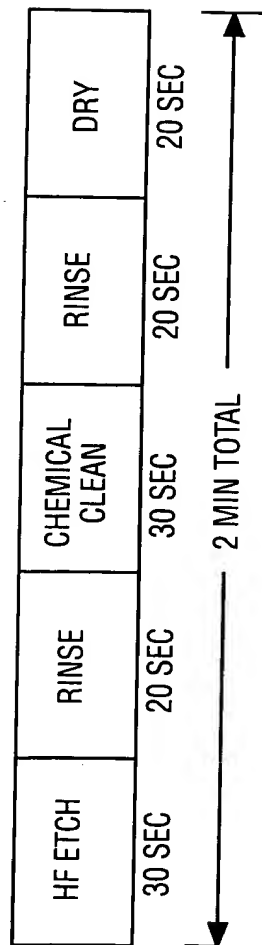


FIG. 1b

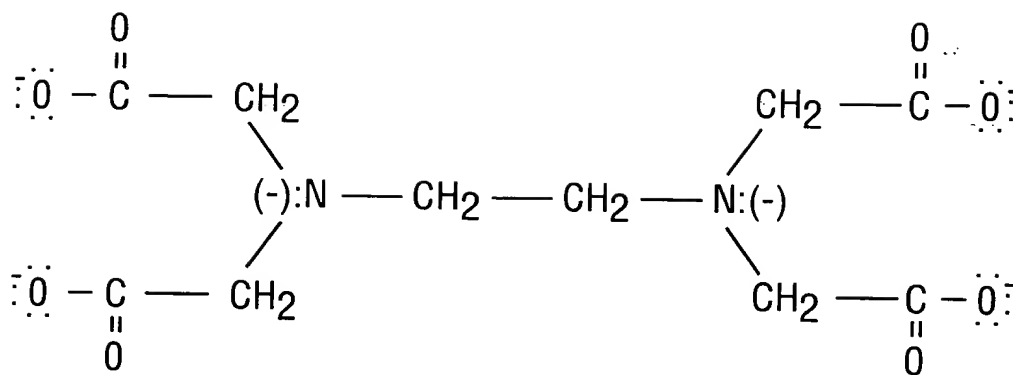


FIG. 2a

\downarrow
 BINDS METAL IONS

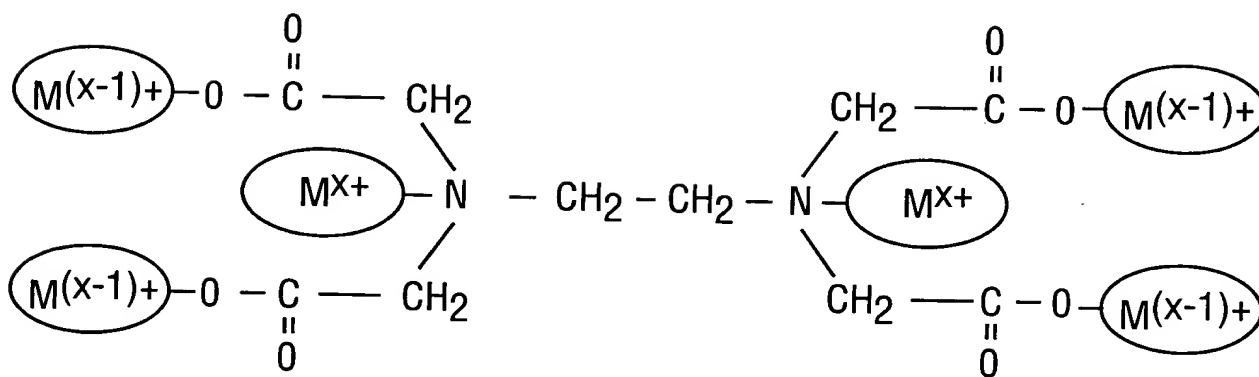
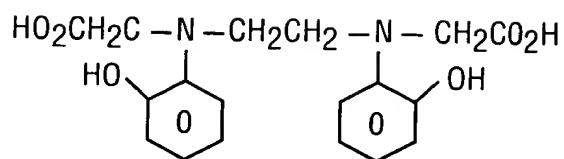
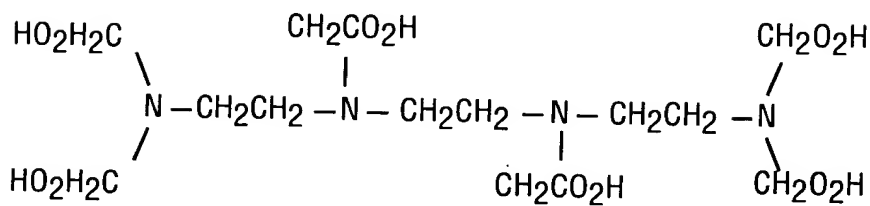


FIG. 2b



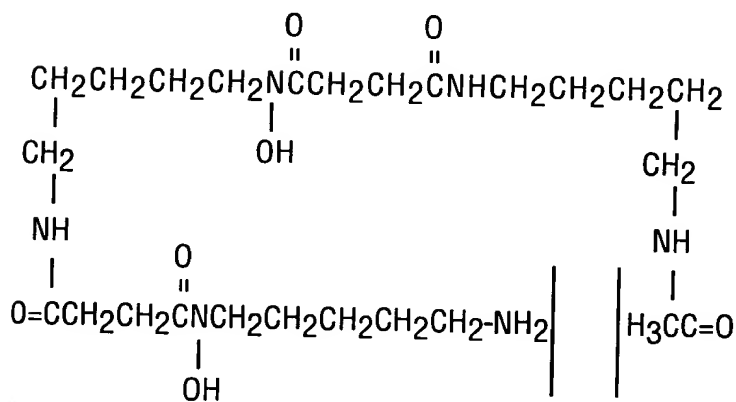
(HPED)

FIG. 3a



(TTHA)

FIG. 3b



DESFERRIFERRIOXAMIN B

FIG. 3c

O=C(NC(=O)CCNC(=O)C1C=CC(=C(C1)CNC(=O)CCNC(=O)O)C)CCNC(=O)O

FIG. 3d

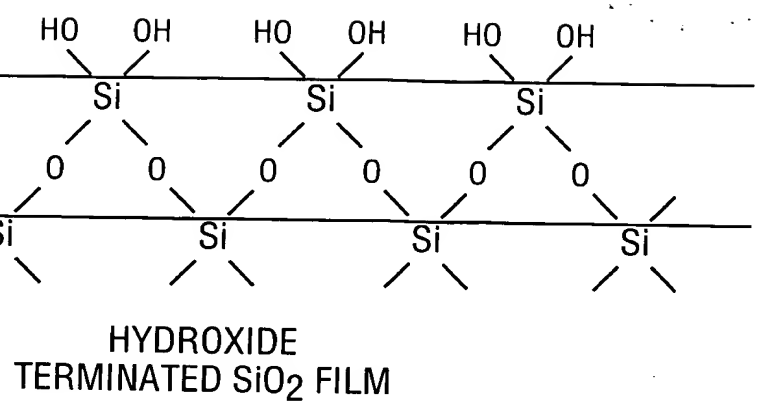


FIG. 4a

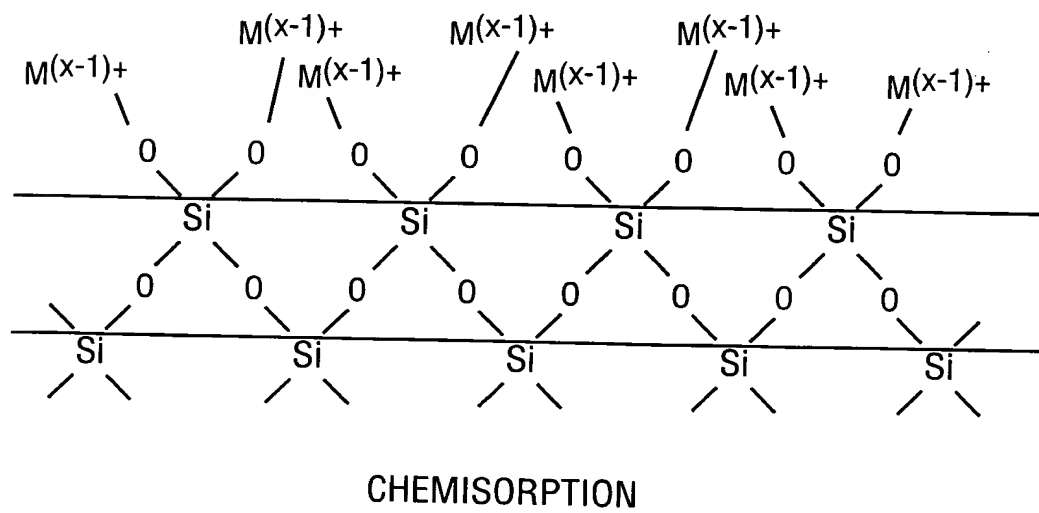


FIG. 4b

The diagram illustrates a particle and a silicon surface. The upper part shows a central oval labeled "PARTICLE" with five wavy lines extending from it to five separate ovals, each labeled SO_4^- . A wavy line labeled "500" points to the "PARTICLE" oval. The lower part shows a horizontal line representing the "SILICON SURFACE 510". Four wavy lines extend from this surface to four separate ovals, each labeled SO_4^- .

FIG. 5

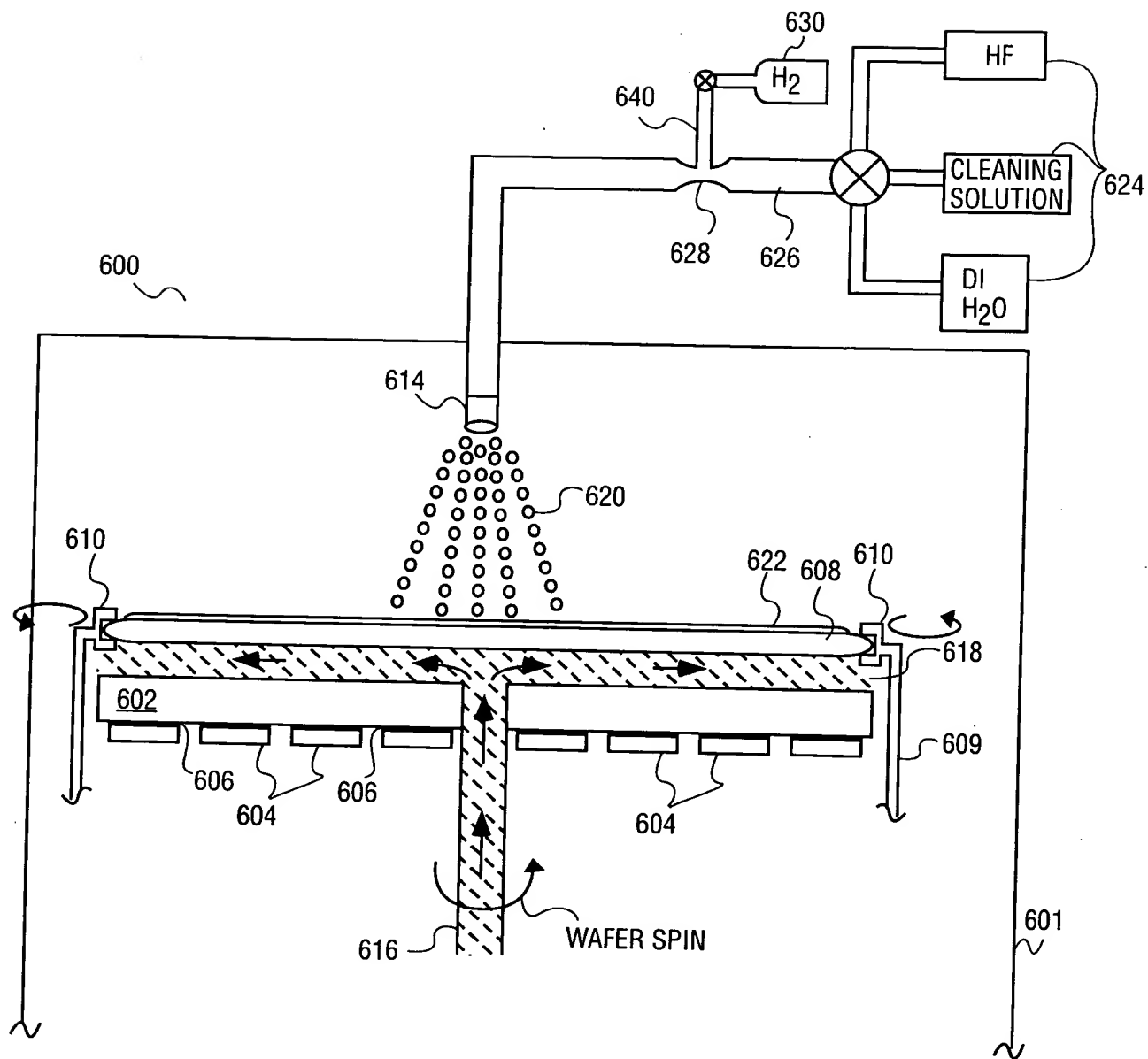


FIG. 6a

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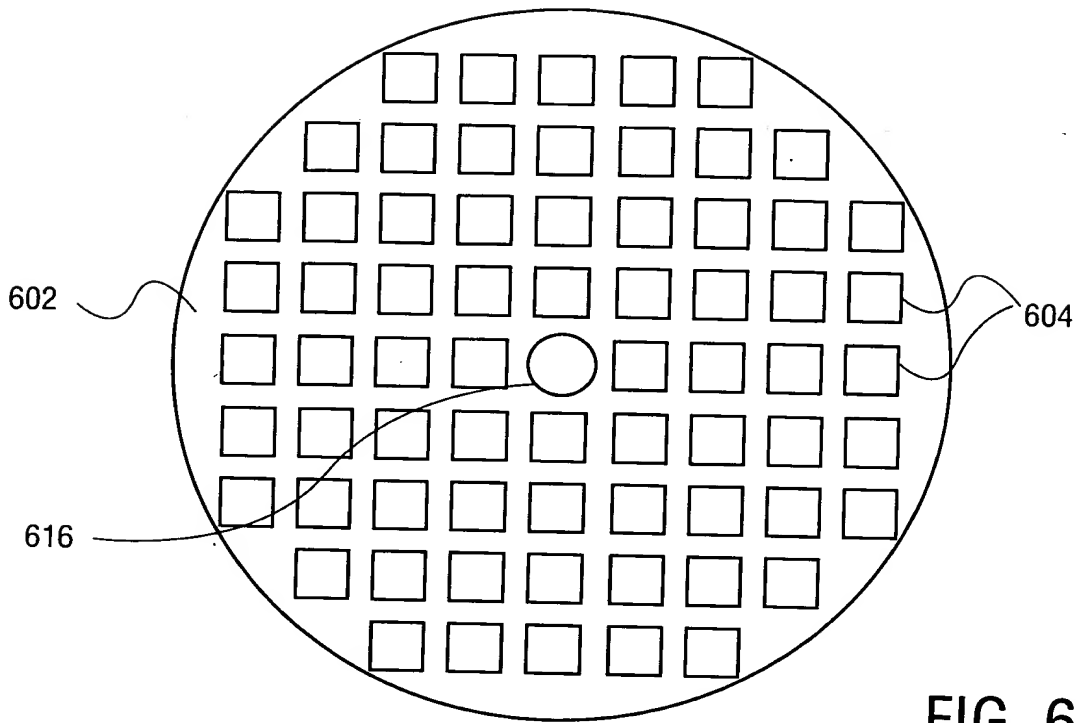


FIG. 6b

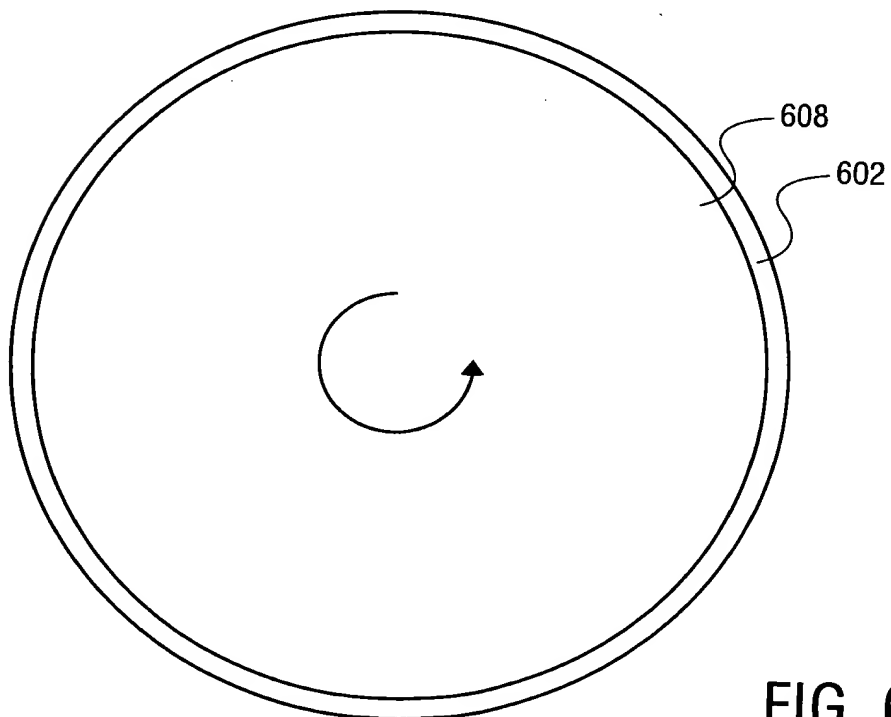


FIG. 6c

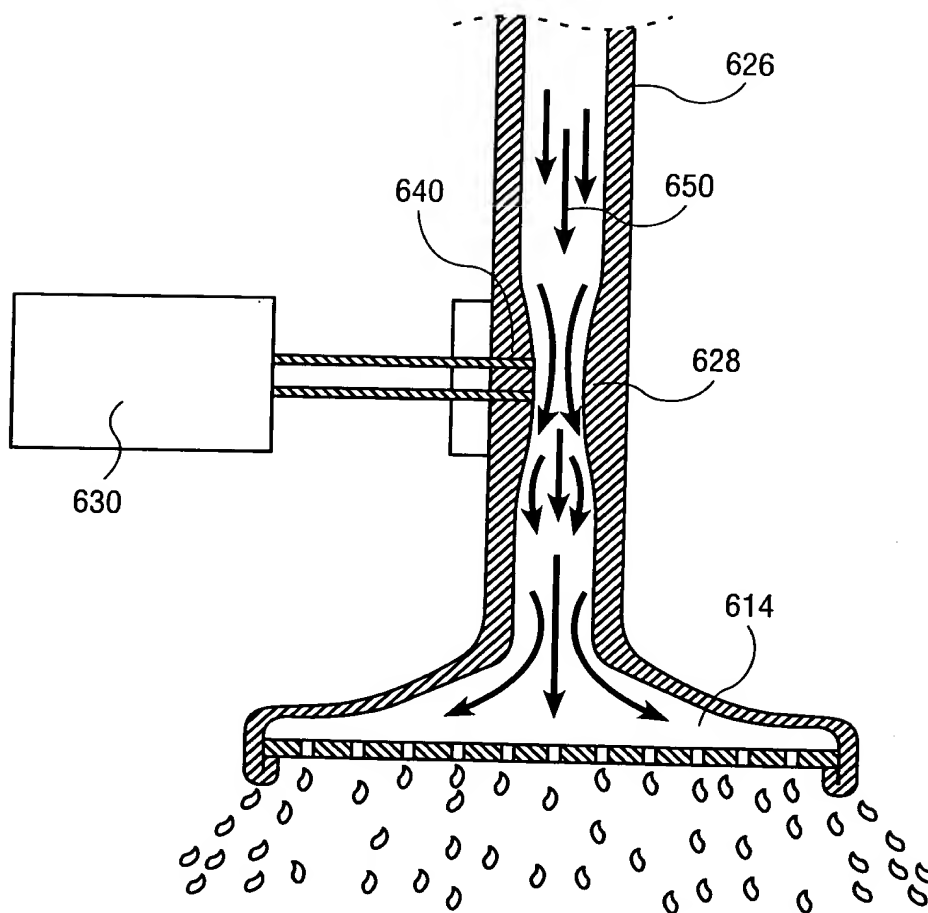


FIG. 6d

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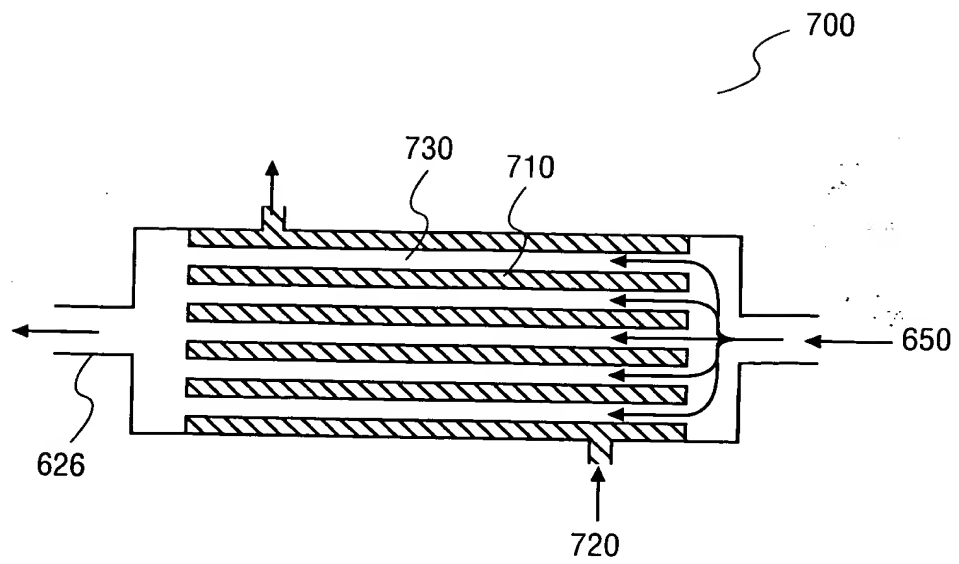


FIG. 7a

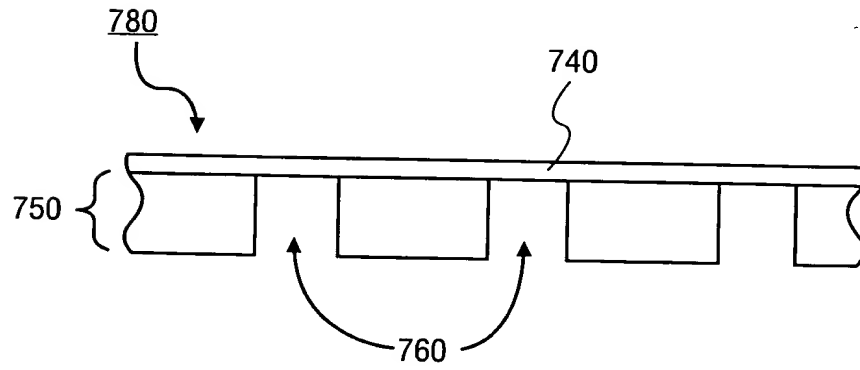


FIG. 7b

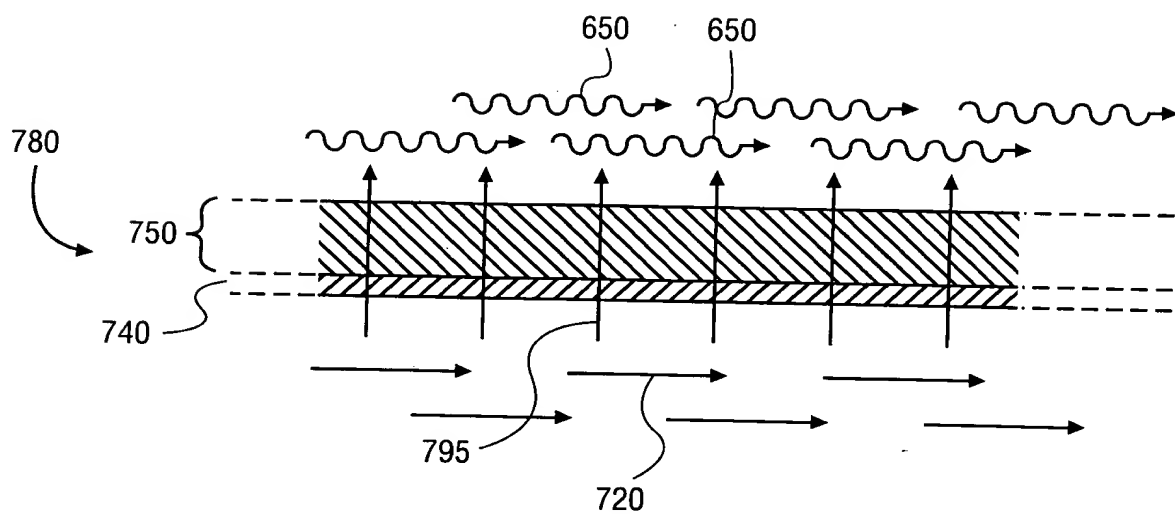


FIG. 7c

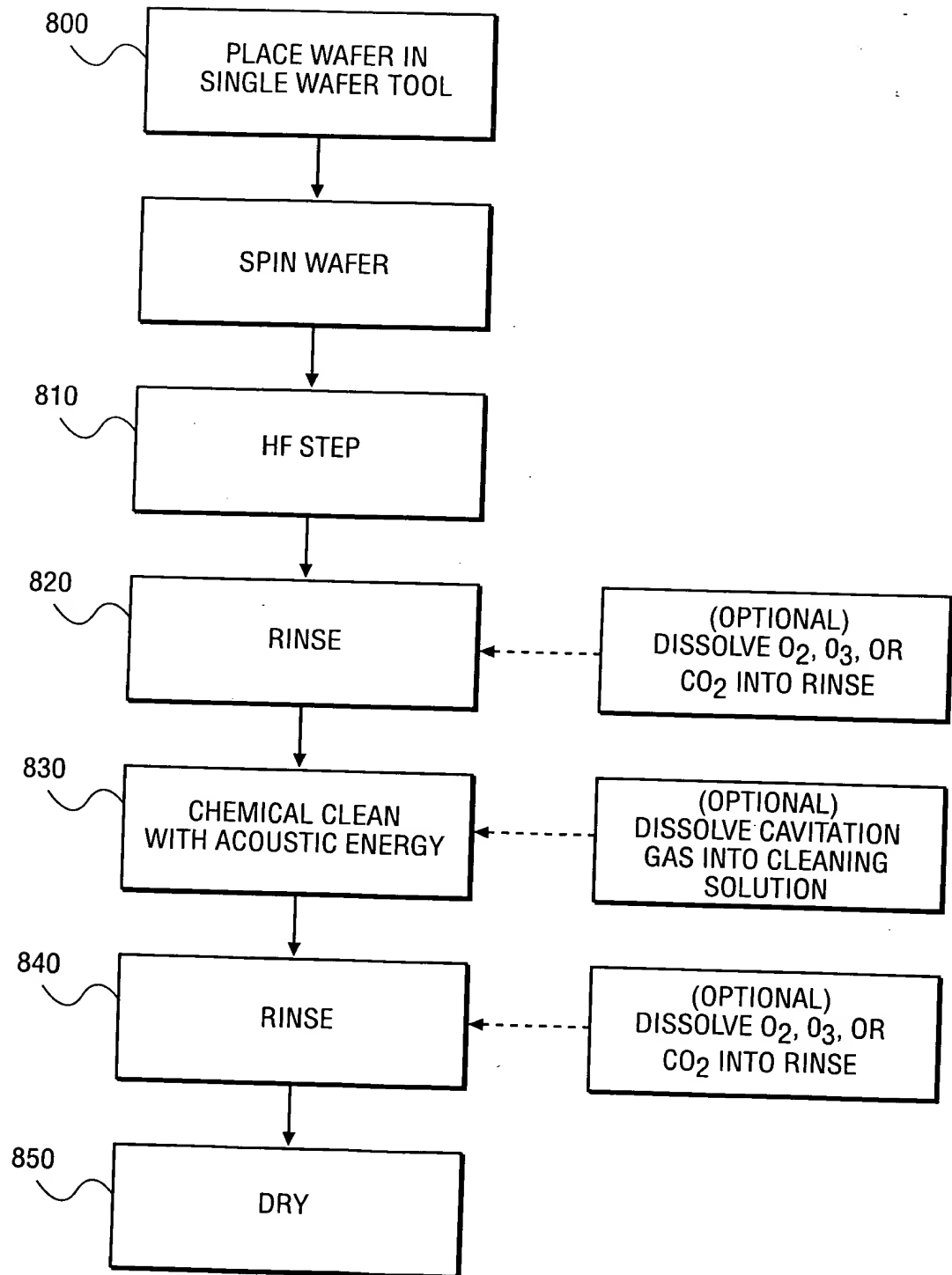


FIG. 8

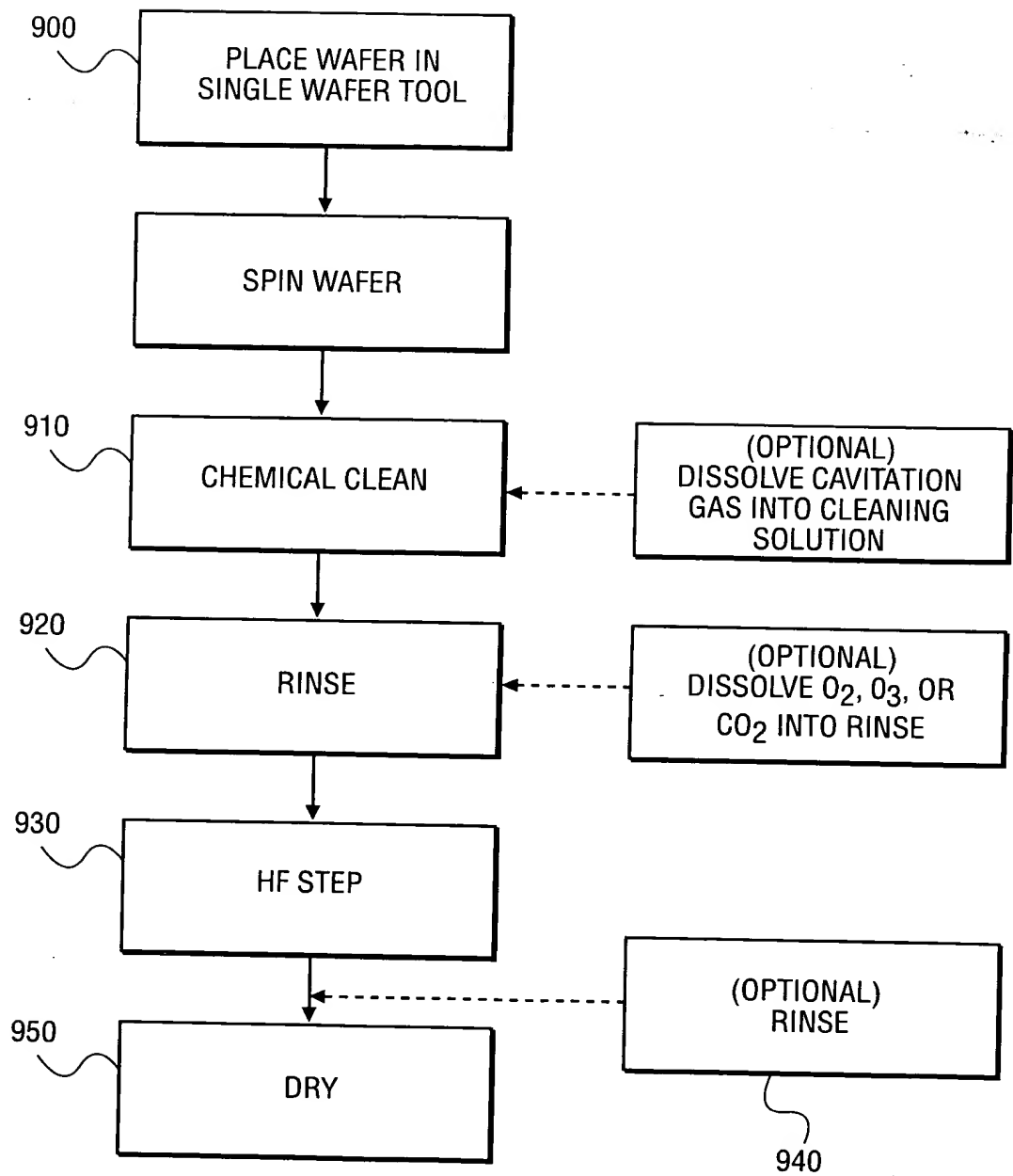


FIG. 9

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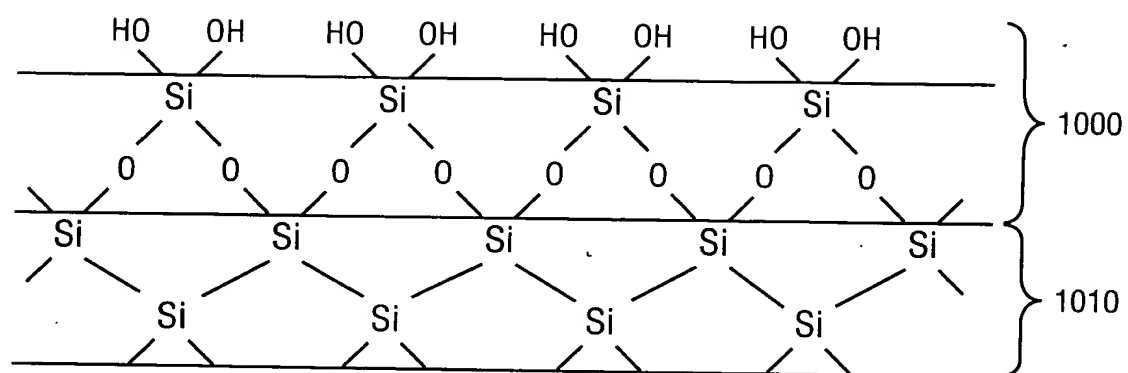
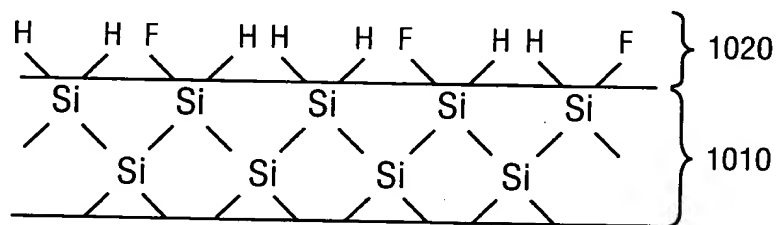


FIG. 10a



HYDROPHOLIC SURFACE

FIG. 10b

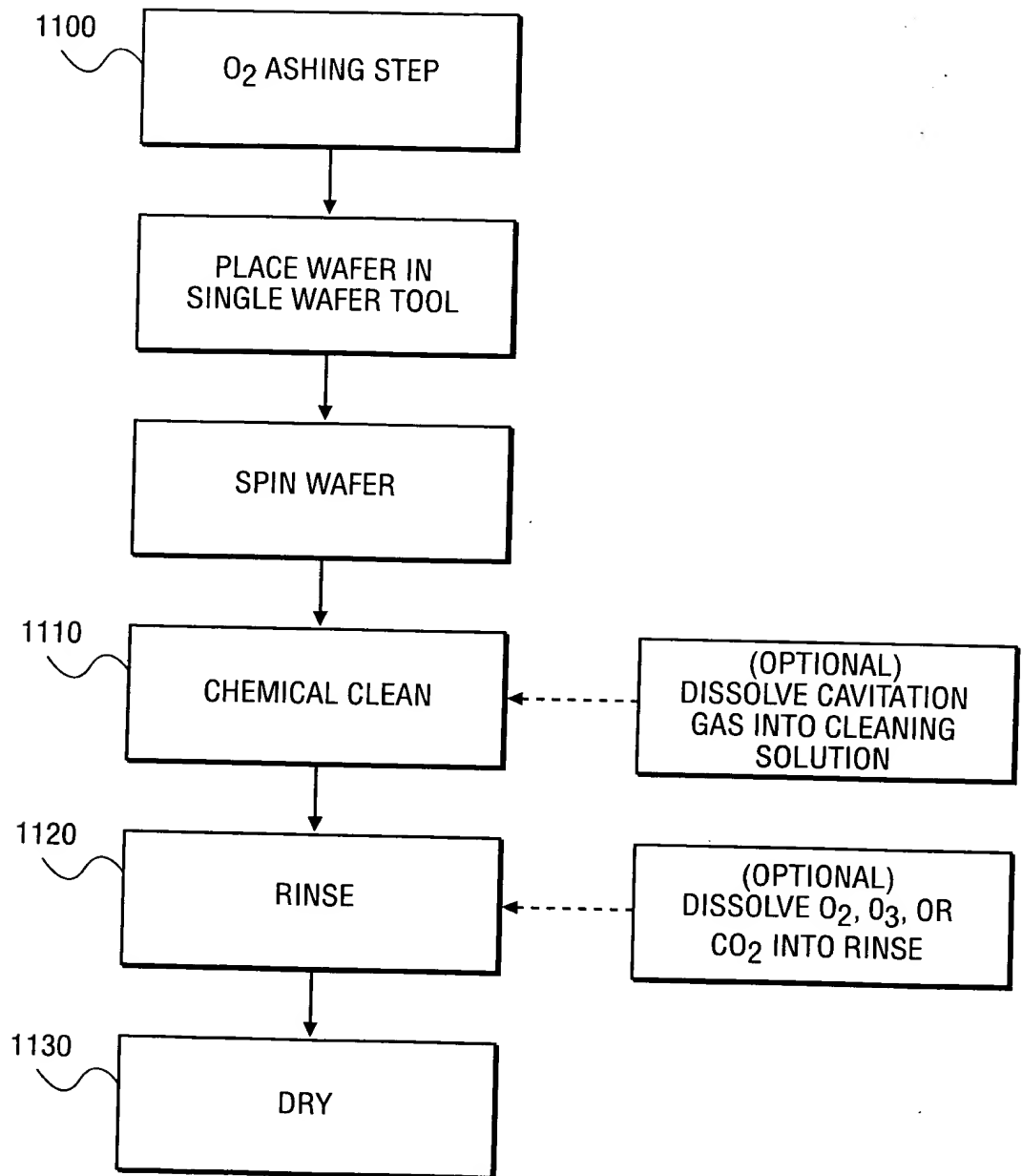


FIG. 11

2007-09-04 09:00

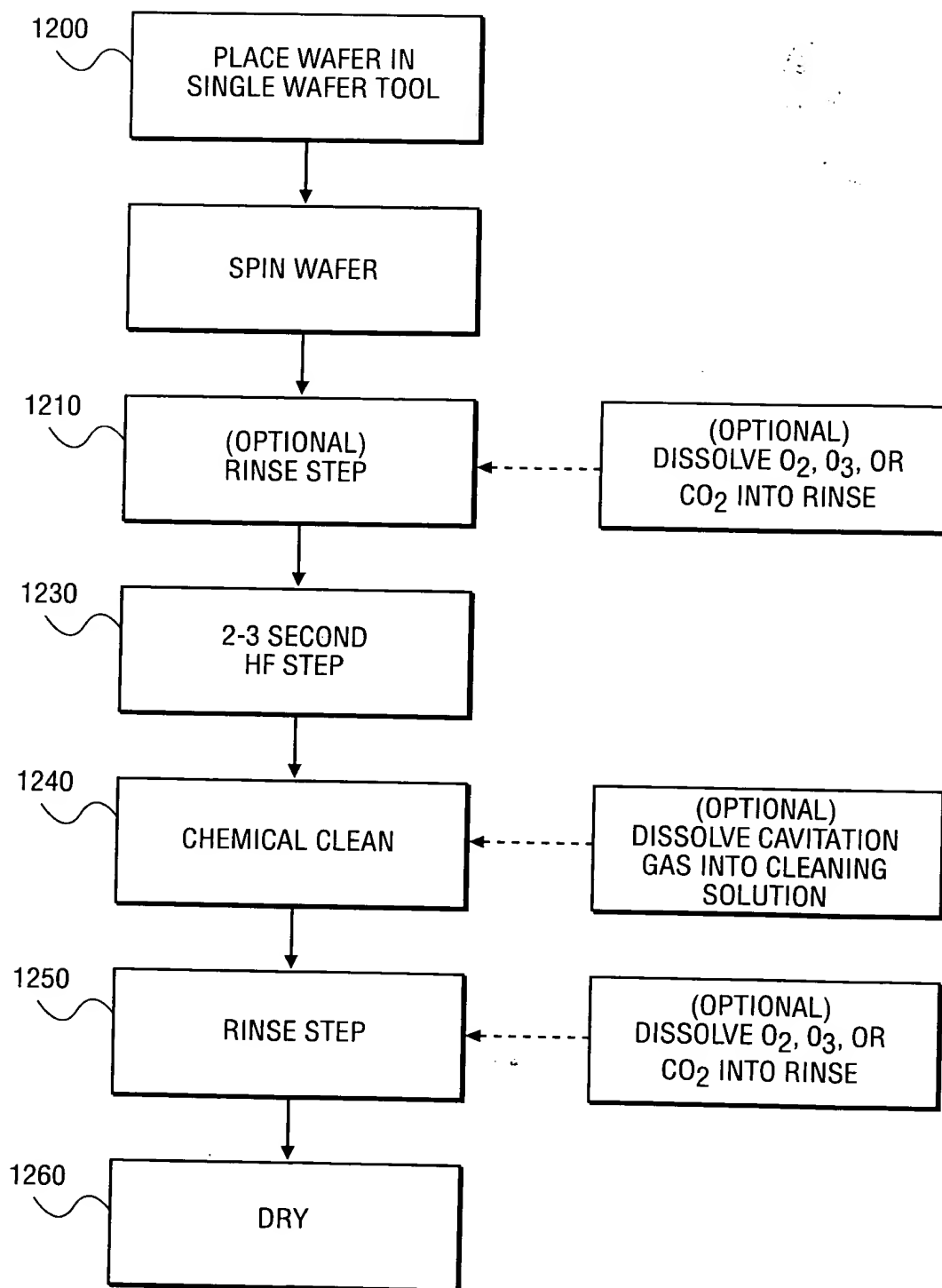


FIG. 12

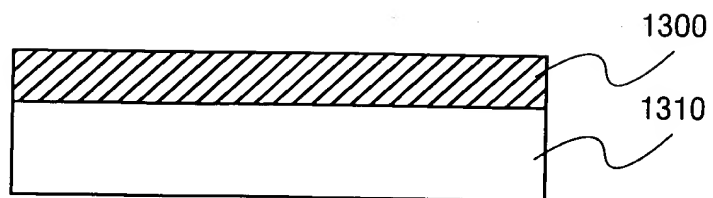


FIG. 13a

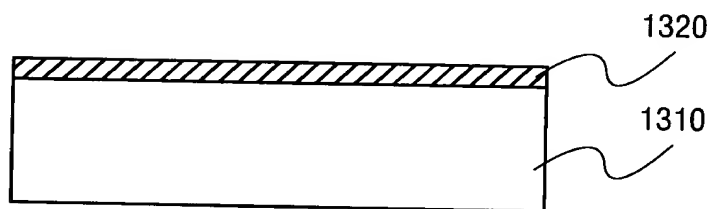


FIG. 13b